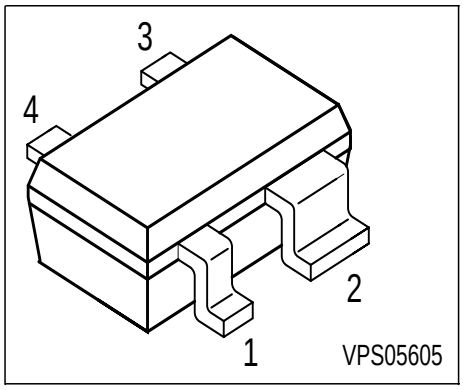
NPN Silicon RF Transistor



- For high gain low noise amplifiers
- For oscillators up to 10 GHz
- Noise figure F = 1.1 dB at 1.8 GHz
  outstanding G_{ms} = 21 dB at 1.8 GHz
- Transition frequency f_T = 25 GHz
- Gold metallization for high reliability
- **SIEGET** ® **25** GHz f_T - **Line**

ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration				Package
BFP420	AMs	1 = B	2 = E	3 = C	4 = E	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	4.5	V
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	35	mA
Base current	I_B	3	
Total power dissipation $T_S \leq 107°C$ 1)	P_{tot}	160	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point2)	R_{thJS}	≤ 260	K/W

1T_S is measured on the emitter lead at the soldering point to the pcb

2For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	4.5	5	-	V
Collector-base cutoff current V_{CB} = 5 V, I_E = 0	I_{CBO}	-	-	200	nA
Emitter-base cutoff current V_{EB} = 1.5 V, I_C = 0	I_{EBO}	-	-	35	µA
DC current gain I_C = 20 mA, V_{CE} = 4 V	h_{FE}	50	100	150	-
AC characteristics (verified by random sampling)					
Transition frequency I_C = 30 mA, V_{CE} = 3 V, f = 2 GHz	f_T	18	25	-	GHz
Collector-base capacitance V_{CB} = 2 V, f = 1 MHz	C_{cb}	-	0.15	0.3	pF
Collector-emitter capacitance V_{CE} = 2 V, f = 1 MHz	C_{ce}	-	0.37	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	0.55	-	
Noise figure I_C = 5 mA, V_{CE} = 2 V, Z_S = Z_{Sopt} , f = 1.8 GHz	F	-	1.1	-	dB
Power gain, maximum stable [1)] I_C = 20 mA, V_{CE} = 2 V, Z_S = Z_{Sopt} , Z_L = Z_{Lopt} , f = 1.8 GHz	G_{ms}	-	21	-	
Insertion power gain I_C = 20 mA, V_{CE} = 2 V, f = 1.8 GHz, Z_S = Z_L = 50Ω	$\lvert S_{21}\rvert^2$	14	17	-	
Third order intercept point I_C = 20 mA, V_{CE} = 2 V, Z_S=Z_{Sopt} , Z_L=Z_{Lopt} , f = 1.8 GHz	IP_3	-	22	-	dBm
1dB Compression point I_C = 20 mA, V_{CE} = 2 V, f = 1.8 GHz, Z_S=Z_{Sopt} , Z_L=Z_{Lopt}	P_{-1dB}	-	12	-	

[1] $G_{ms} = |S_{21} / S_{12}|$

SPICE Parameters (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax) :

Transistor Chip Data

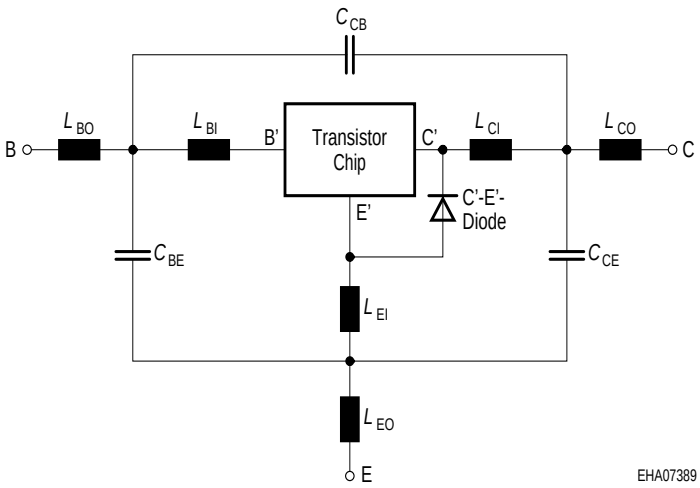
IS =	0.20045	fA	BF =	72.534	-	NF =	1.2432	-
VAF =	28.383	V	IKF =	0.48731	A	ISE =	19.049	fA
NE =	2.0518	-	BR =	7.8287	-	NR =	1.3325	-
VAR =	19.705	V	IKR =	0.69141	A	ISC =	0.019237	fA
NC =	1.1724	-	RB =	8.5757	Ω	IRB =	0.72983	mA
RBM =	3.4849	Ω	RE =	0.31111		RC =	0.10105	Ω
CJE =	1.8063	fF	VJE =	0.8051	V	MJE =	0.46576	-
TF =	6.7661	ps	XTF =	0.42199	-	VTF =	0.23794	V
ITF =	1	mA	PTF =	0	deg	CJC =	234.53	fF
VJC =	0.81969	V	MJC =	0.30232	-	XCJC =	0.3	-
TR =	2.3249	ns	CJS =	0	F	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.73234	-	TNOM	300	K

C'-E'-Diode Data (Berkley-SPICE 2G.6 Syntax) :

IS =	3.5	fA	N =	1.02	-	RS =	10	Ω

All parameters are ready to use, no scaling is necessary

Package Equivalent Circuit:



L_{BI} =	0.47	nH
L_{BO} =	0.53	nH
L_{EI} =	0.23	nH
L_{EO} =	0.05	nH
L_{CI} =	0.56	nH
L_{CO} =	0.58	nH
C_{BE} =	136	fF
C_{CB} =	6.9	fF
C_{CE} =	134	fF

Valid up to 6GHz

The SOT-343 package has two emitter leads. To avoid high complexity of the package equivalent circuit, both leads are combined in one electrical connection.

Extracted on behalf of Infineon Technologies AG by:
Institut für Mobil-und Satellitentechnik (IMST)

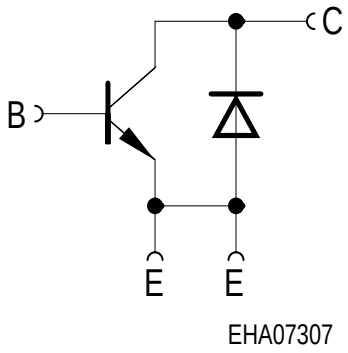
For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet:
http://www.infineon.com/silicondiscretes

For non-linear simulation:

- Use transistor chip parameters in Berkeley SPICE 2G.6 syntax for all simulators.
- If you need simulation of the reverse characteristics, add the diode with the C'-E'- diode data between collector and emitter.
- Simulation of package is not necessary for frequencies < 100MHz. For higher frequencies add the wiring of package equivalent circuit around the non-linear transistor and diode model.

Note:

- This transistor is constructed in a common emitter configuration. This feature causes an additional reverse biased diode between emitter and collector, which does not effect normal operation.



Transistor Schematic Diagram

The common emitter configuration shows the following advantages:

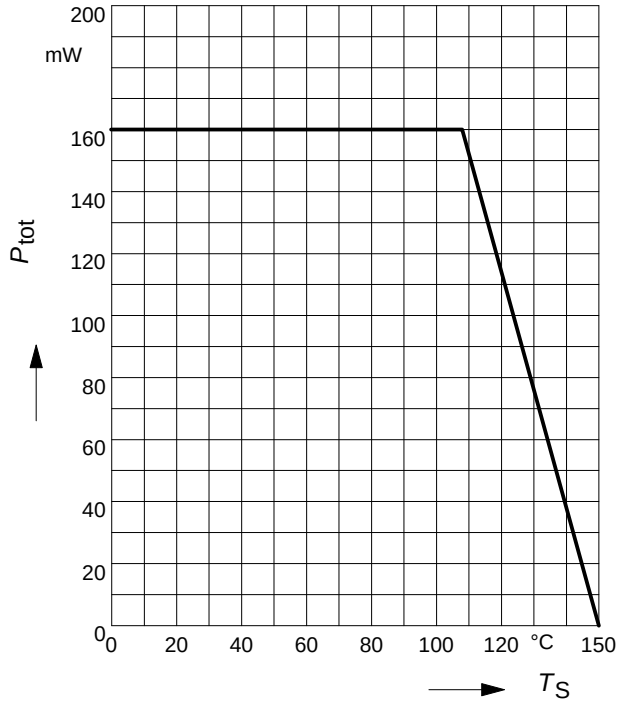
- Higher gain because of lower emitter inductance.
- Power is dissipated via the grounded emitter leads, because the chip is mounted on copper emitter leadframe.

Please note, that the broadest lead is the emitter lead.

Common Emitter S- and Noise-parameter

For detailed S- and Noise-parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies Application Notes CD-ROM or see Internet: http://www.infineon.com/silicondiscretes

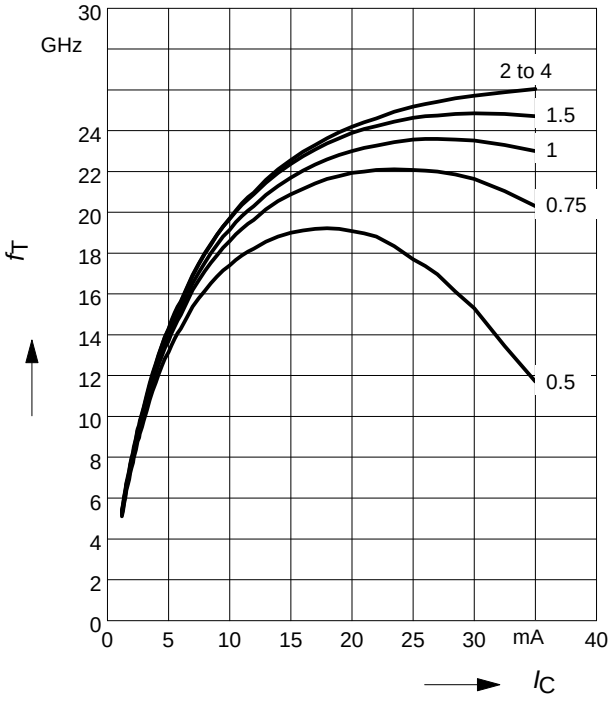
Total power dissipation $P_{tot} = f(T_S)$



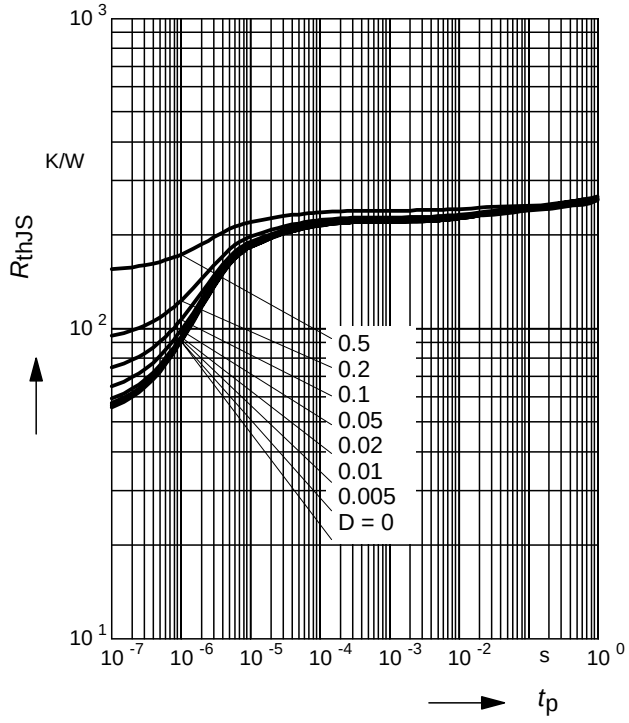
Transition frequency $f_T = f(I_C)$

f = 2 GHz

V_{CE} = parameter in V

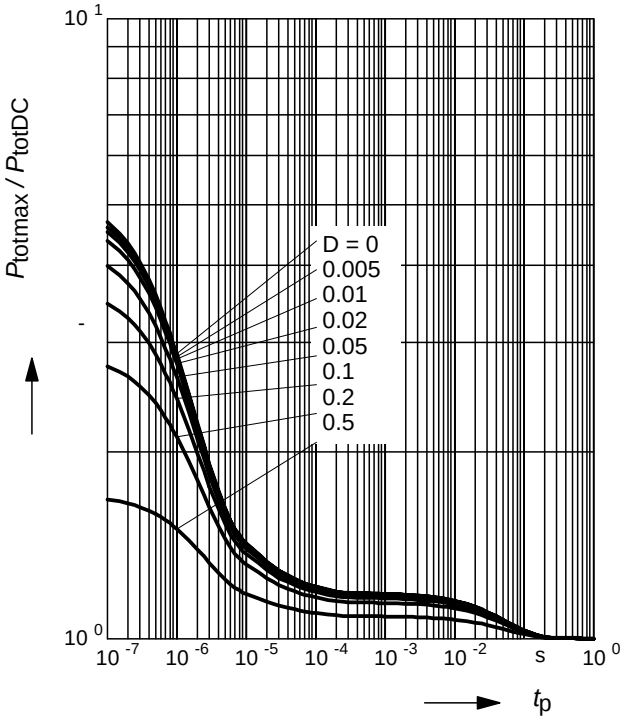


Permissible Pulse Load $R_{thJS} = f(t_p)$

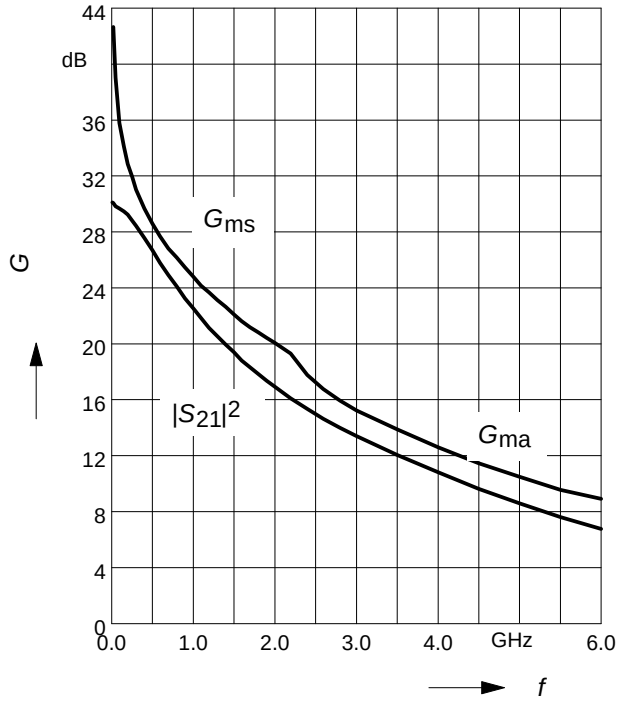


Permissible Pulse Load

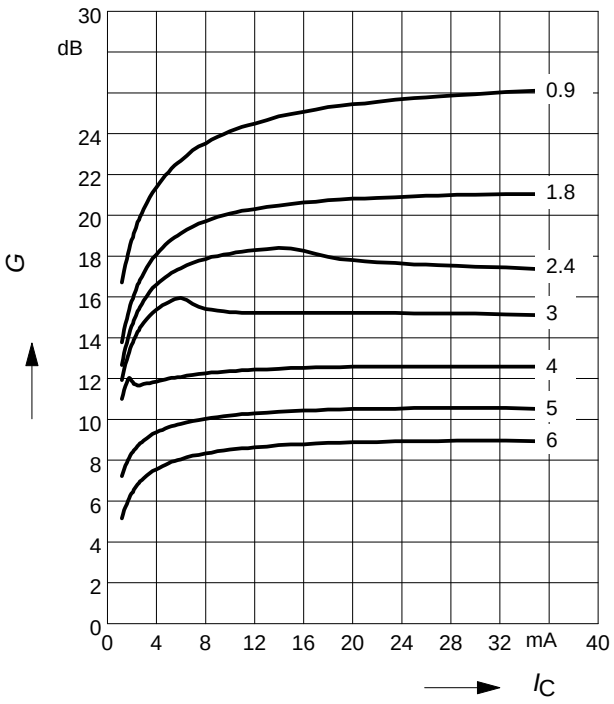
$P_{totmax}/P_{totDC} = f(t_p)$



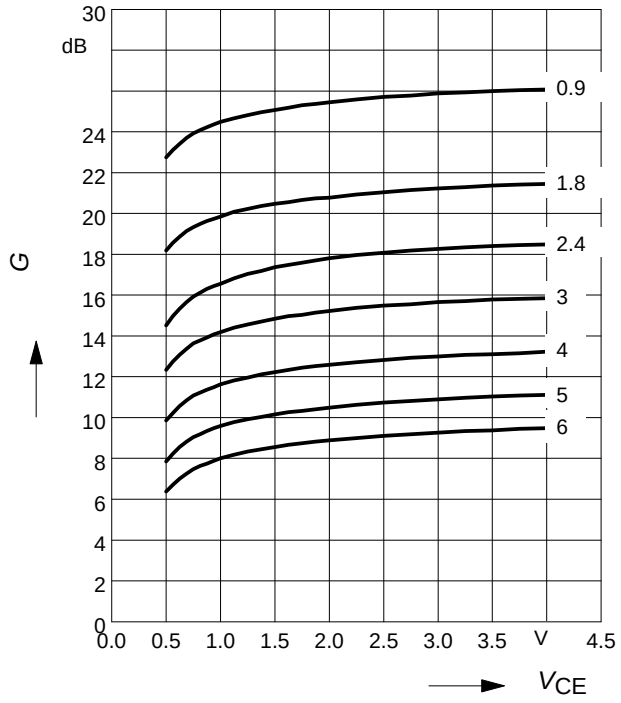
Power gain G_{ma}, G_{ms}, $|S_{21}|^2 = f(f)$
V_{CE} = 2V, I_C = 20 mA



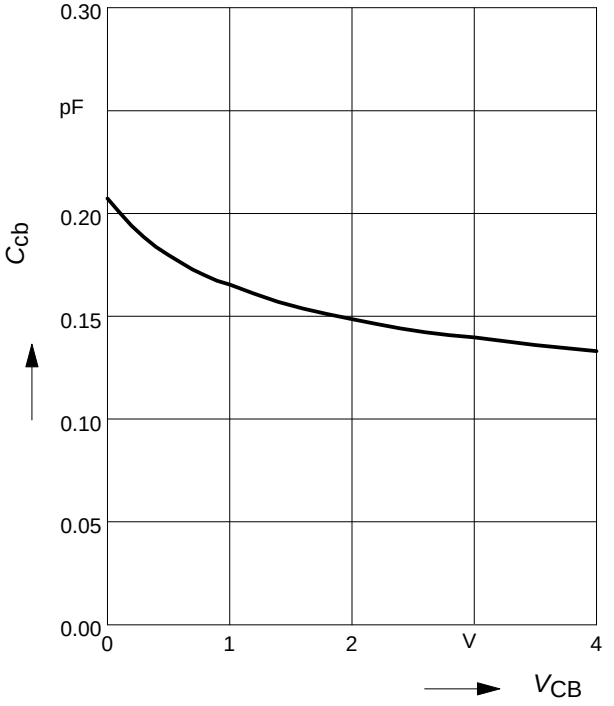
Power gain G_{ma}, $G_{ms} = f(I_C)$
V_{CE} = 2V
f = parameter in GHz



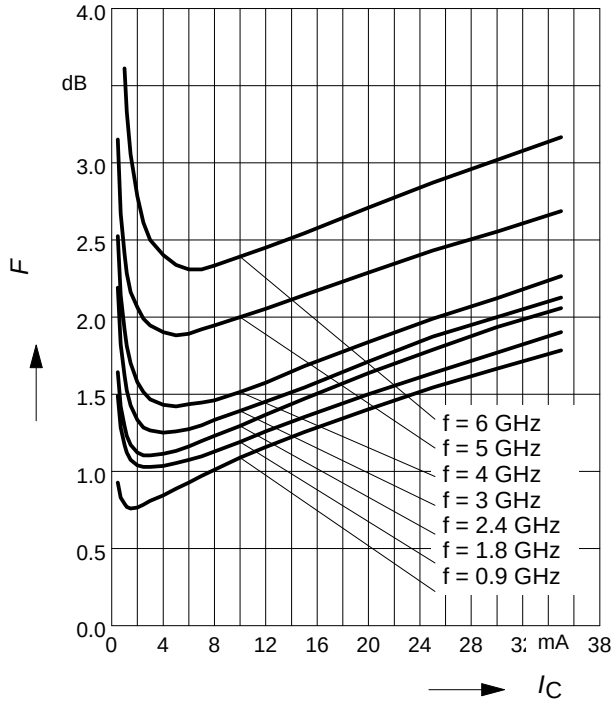
Power gain G_{ma}, $G_{ms} = f(V_{CE})$
I_C = 20 mA
f = parameter in GHz



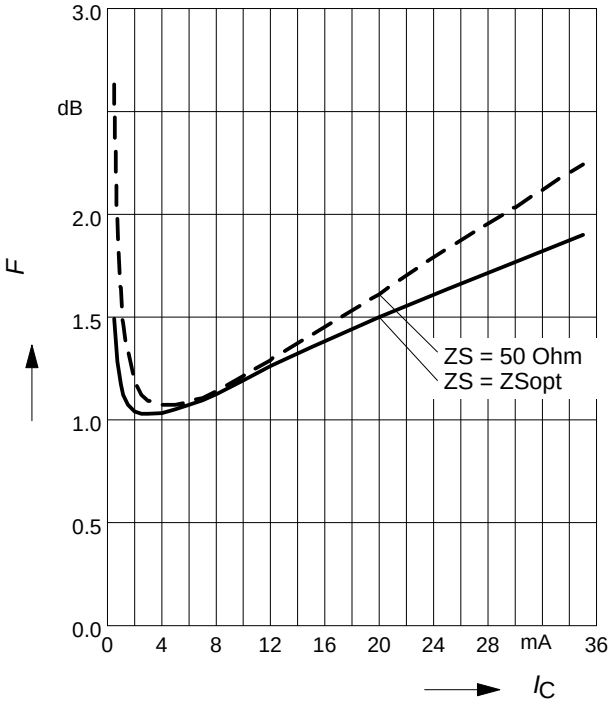
Collector-base capacitance $C_{cb} = f(V_{CB})$
f = 1MHz



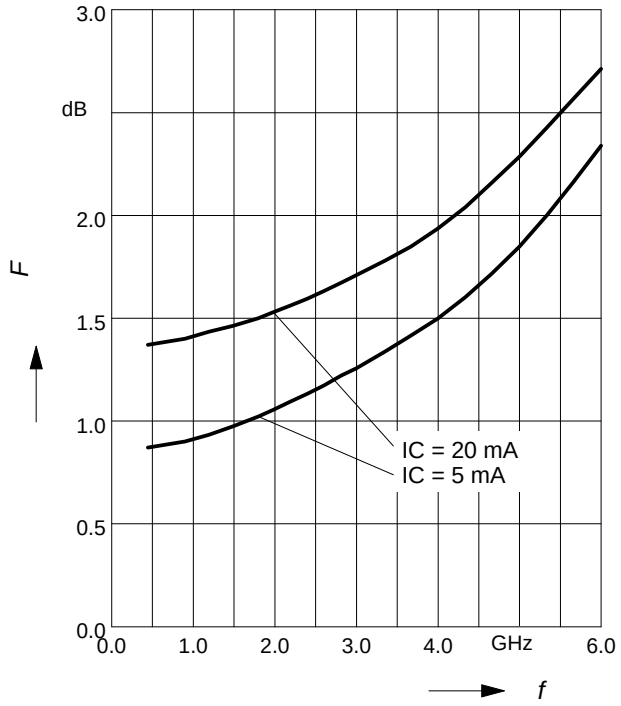
Noise figure $F = f(I_C)$
V_{CE} = 2 V, $Z_S = Z_{Sopt}$



Noise figure $F = f(I_C)$
V_{CE} = 2 V, f = 1.8 GHz



Noise figure $F = f(f)$
V_{CE} = 2 V, $Z_S = Z_{Sopt}$



Source impedance for min.
Noise Figure versus Frequency
V_{CE} = 2 V, I_C = 5 mA / 20 mA

